

ABSTRACT

A method and system for providing a semiconductor memory device is disclosed.

The method and system include providing a plurality of gate stacks above a substrate. Each of the plurality of gate stacks includes a first edge and a second edge. The method and system also include providing a source implant adjacent to the first edge of each of the plurality of gate stacks and driving the source implant under the first edge of each of the plurality of gate stacks. The method and system also include providing a drain implant after source implant is driven under the first edge. The drain implant is in the substrate adjacent to the second edge of each of the plurality of gate stacks.